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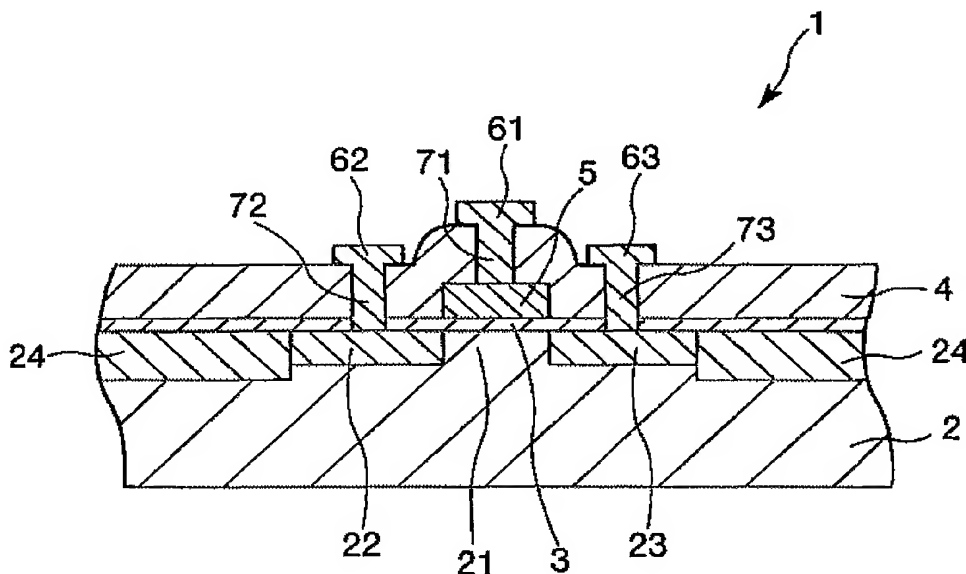
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[Continued on next page]

(54) Title: A SEMICONDUCTOR DEVICE, AN ELECTRONIC DEVICE AND AN ELECTRONIC APPARATUS



(57) Abstract: A semiconductor device 1 includes: a base 2 mainly formed of a semiconductor material; a gate electrode 5; and a gate insulating film 3 provided between the base 2 and the gate electrode 5. The gate insulating film 3 is formed of an insulative inorganic material containing silicon, oxygen and element X other than silicon and oxygen as a main material. The gate insulating film 3 is provided in contact with the base 2, and contains hydrogen atoms. The gate insulating film 3 has a region where A and B satisfy the relation: B/A is 10 or less in the case where the total concentration of the element X in the region is defined as A and the total concentration of hydrogen in the region is defined as B. Further, the region is at least a part of the gate insulating film 3 in the thickness direction thereof.

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